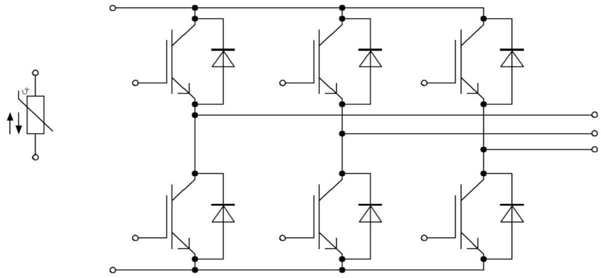
FS200R12KT4RP

EconoPACK™3 模块 采用第四代沟槽栅/场终止IGBT4和第四代发射极控制二极管 带有温度检测NTC和预涂导热介质

EconoPACK™3 module with Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode and NTC / pre-applied Thermal Interface Material

Typical appearance



V_{CES} = 1200V

$I_{C\ nom}$ = 200A / I_{CRM} = 400A

潜在应用

- 伺服驱动器
- 电机传动
- 辅助逆变器

Potential Applications

- Servo drives
- Motor drives
- Auxiliary inverters

电气特性

- $T_{vj\ op}$ = 150°C
- V_{CEsat} 带正温度系数
- 低 V_{CEsat}
- 低开关损耗

Electrical Features

- $T_{vj\ op}$ = 150°C
- V_{CEsat} with positive temperature coefficient
- Low V_{CEsat}
- Low switching losses

机械特性

- 标准封装
- 焊接技术
- 铜基板
- 集成NTC温度传感器
- 预涂导热介质
- 高功率循环和温度循环能力

Mechanical Features

- Standard housing
- Solder contact technology
- Copper base plate
- Integrated NTC temperature sensor
- Pre-applied Thermal Interface Material
- High power and thermal cycling capability

Module Label Code

Barcode Code 128

00000123456000000000000

DMX - Code

Content of the Code	**Digit**
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT,Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	T_H = 60°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$	200	A
集电极重复峰值电流 Repetitive peak collector current	t_P = 1 ms	I_{CRM}	400	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

				min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	I_C = 200 A, V_{GE} = 15 V I_C = 200 A, V_{GE} = 15 V I_C = 200 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE\,sat}$		1,75 2,05 2,10	2,15	V V V
栅极阈值电压 Gate threshold voltage	I_C = 7,60 mA, V_{CE} = V_{GE}, T_{vj} = 25°C		V_{GEth}	5,20	5,80	6,40	V
栅极电荷 Gate charge	V_{GE} = -15 V ... +15 V		Q_G		1,65		µC
内部栅极电阻 Internal gate resistor	T_{vj} = 25°C		R_{Gint}		3,5		Ω
输入电容 Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		14,0		nF
反向传输电容 Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{res}		0,50		nF
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE} = 1200 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	I_C = 200 A, V_{CE} = 600 V V_{GE} = ±15 V R_{Gon} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,on}$		0,14 0,15 0,15		µs µs µs
上升时间(电感负载) Rise time, inductive load	I_C = 200 A, V_{CE} = 600 V V_{GE} = ±15 V R_{Gon} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0,03 0,035 0,04		µs µs µs
关断延迟时间(电感负载) Turn-off delay time, inductive load	I_C = 200 A, V_{CE} = 600 V V_{GE} = ±15 V R_{Goff} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,off}$		0,32 0,40 0,42		µs µs µs
下降时间(电感负载) Fall time, inductive load	I_C = 200 A, V_{CE} = 600 V V_{GE} = ±15 V R_{Goff} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0,09 0,16 0,18		µs µs µs
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	I_C = 200 A, V_{CE} = 600 V, L_S = 30 nH V_{GE} = ±15 V, di/dt = 5400 A/µs (T_{vj} = 150°C) R_{Gon} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		10,5 18,5 20,5		mJ mJ mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	I_C = 200 A, V_{CE} = 600 V, L_S = 30 nH V_{GE} = ±15 V, du/dt = 5000 V/µs (T_{vj} = 150°C) R_{Goff} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		11,0 16,5 18,5		mJ mJ mJ
短路数据 SC data	V_{GE} ≤ 15 V, V_{CC} = 800 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt	t_P ≤ 10 µs, T_{vj} = 150°C	I_{SC}		720		A
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个 IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}			0,216	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

二极管,逆变器 / Diode, Inverter

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	200	A
正向重复峰值电流 Repetitive peak forward current	t_P = 1 ms	I_{FRM}	400	A
I2t-值 I^2t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I^2t	5200 5000	A^2s A^2s

特征值 / Characteristic Values

				min.	typ.	max.	
正向电压 Forward voltage	I_F = 200 A, V_{GE} = 0 V I_F = 200 A, V_{GE} = 0 V I_F = 200 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,65 1,65 1,65	2,10	V V V
反向恢复峰值电流 Peak reverse recovery current	I_F = 200 A, - di_F/dt = 5400 A/µs (T_{vj}=150°C) V_R = 600 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		240 250 260		A A A
恢复电荷 Recovered charge	I_F = 200 A, - di_F/dt = 5400 A/µs (T_{vj}=150°C) V_R = 600 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		18,5 33,5 38,5		µC µC µC
反向恢复损耗(每脉冲) Reverse recovery energy	I_F = 200 A, - di_F/dt = 5400 A/µs (T_{vj}=150°C) V_R = 600 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		8,10 14,5 16,0		mJ mJ mJ
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material		R_{thJH}			0,322	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	T_{NTC} = 25°C	R_{25}		5,00		kΩ
R100 偏差 Deviation of R100	T_{NTC} = 100°C, R_{100} = 493 Ω	ΔR/R	-5		5	%
耗散功率 Power dissipation	T_{NTC} = 25°C	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25}$ exp $[B_{25/50}(1/T_2 - 1/(298,15\ K))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25}$ exp $[B_{25/80}(1/T_2 - 1/(298,15\ K))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25}$ exp $[B_{25/100}(1/T_2 - 1/(298,15\ K))]$	$B_{25/100}$		3433		K

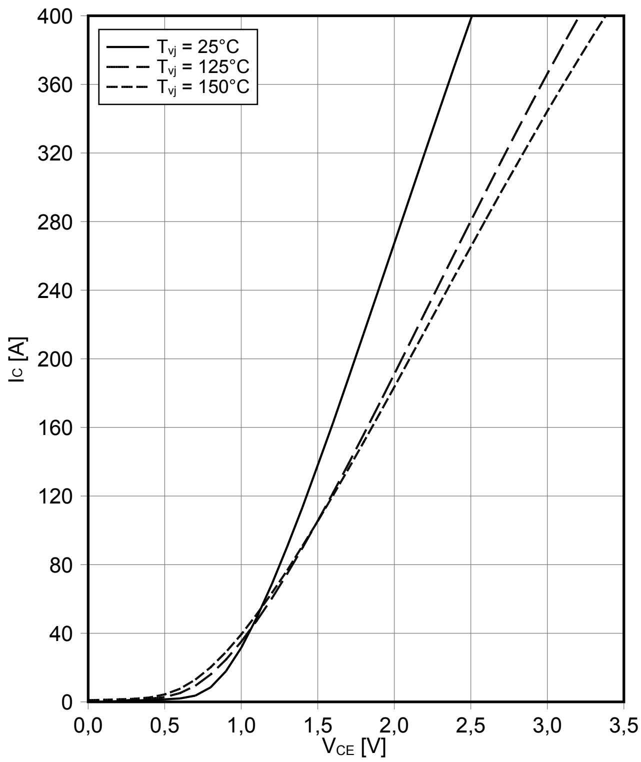
根据应用手册标定
Specification according to the valid application note.

模块 / Module

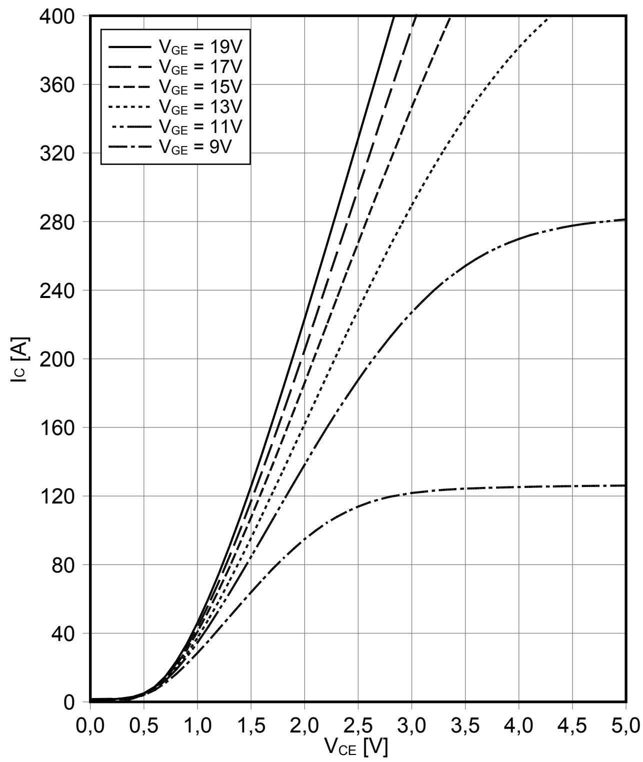
绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}		2,5		kV
模块基板材料 Material of module baseplate				Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)			Al_2O_3		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal			10,0		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal			7,5		mm
相对电痕指数 Comperative tracking index		CTI		> 200		
			min.	typ.	max.	
杂散电感,模块 Stray inductance module		L_{sCE}		21		nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T_H = 25°C, 每个开关 / per switch	$R_{CC'+EE'}$		1,80		mΩ
储存温度 Storage temperature		T_{stg}	-40		125	°C
最高基板工作温度 Maximum baseplate operation temperature		T_{BPmax}			125	°C
模块安装的安装扭距 Mounting torque for modul mounting	螺丝 M5 根据相应的应用手册进行安装 Screw M5 - Mounting according to valid application note	M	3,00		6,00	Nm
重量 Weight		G		300		g

Der Strom im Dauerbetrieb ist auf 50 A effektiv pro Anschlusspin begrenzt.
The current under continuous operation is limited to 50 A rms per connector pin.
Lagerung und Transport von Modulen mit TIM => siehe AN2012-07
Storage and shipment of modules with TIM => see AN2012-07

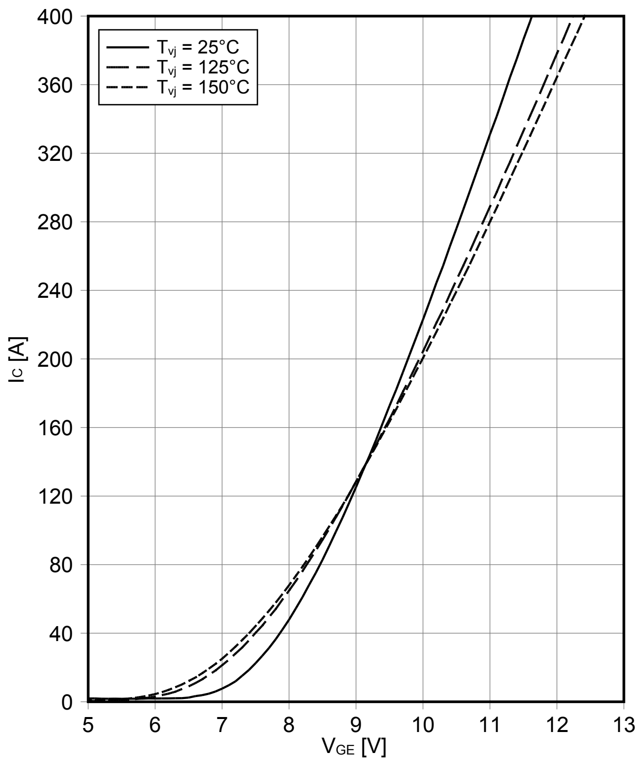
输出特性 IGBT, 逆变器 （典型)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V



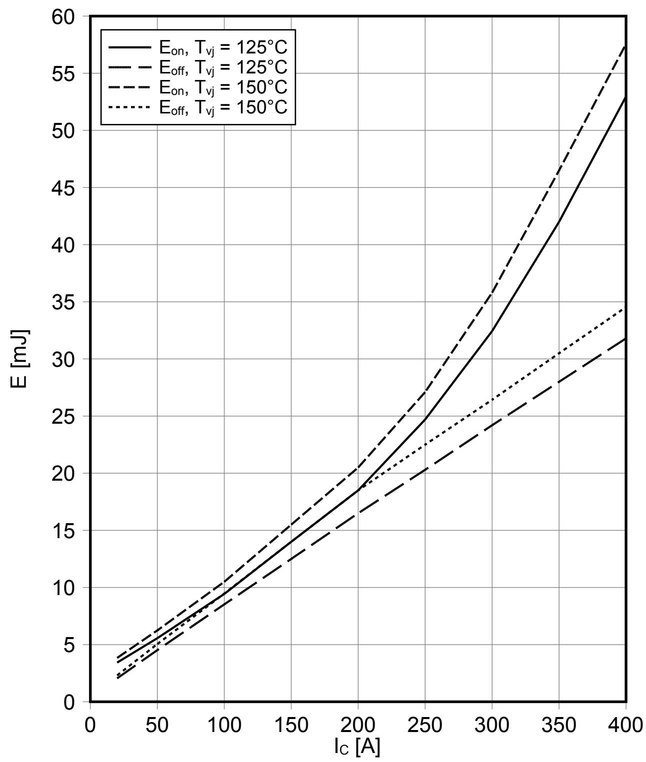
输出特性 IGBT, 逆变器 （典型)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150°C$



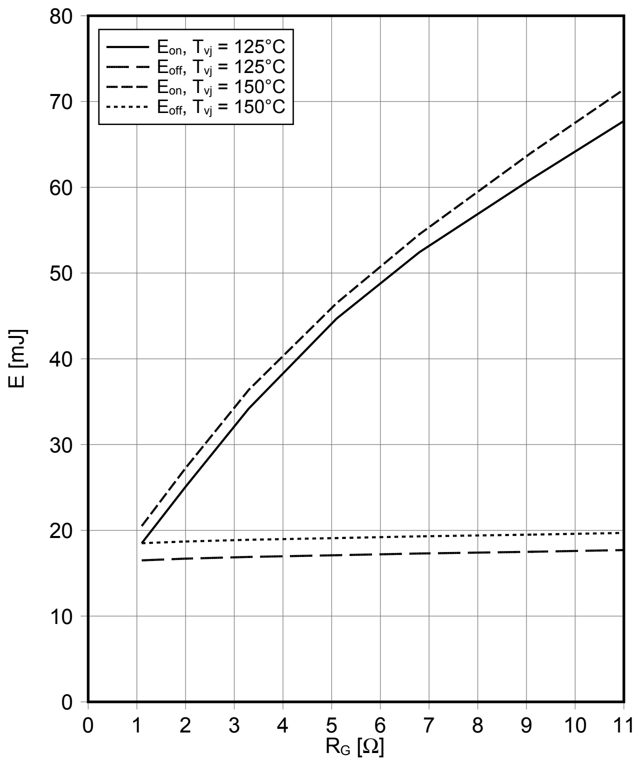
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT,Inverter (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



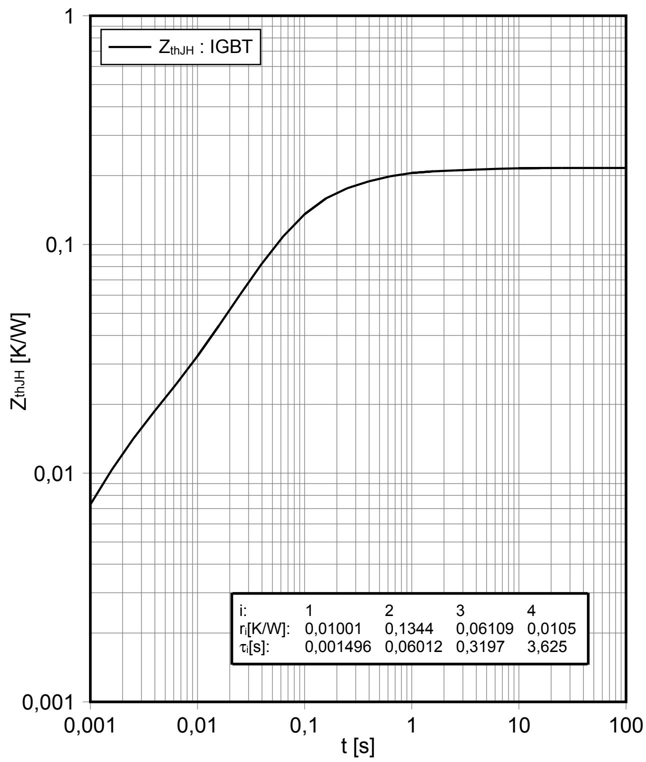
开关损耗 IGBT, 逆变器 （典型)
switching losses IGBT,Inverter (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$V_{GE} = \pm 15$ V, $R_{Gon} = 1.1\ \Omega$, $R_{Goff} = 1.1\ \Omega$, $V_{CE} = 600$ V



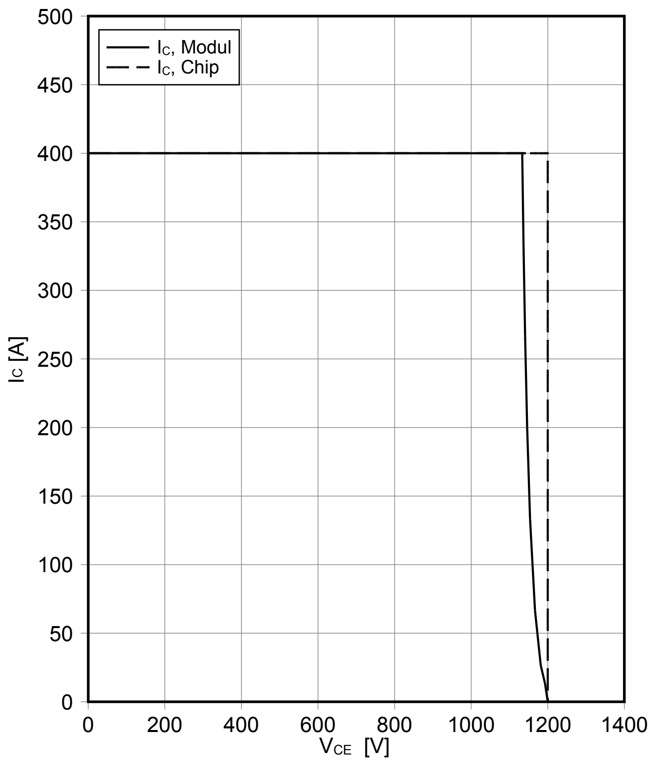
开关损耗 IGBT, 逆变器 （典型)
switching losses IGBT,Inverter (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
$V_{GE} = \pm15$ V, $I_C = 200$ A, $V_{CE} = 600$ V



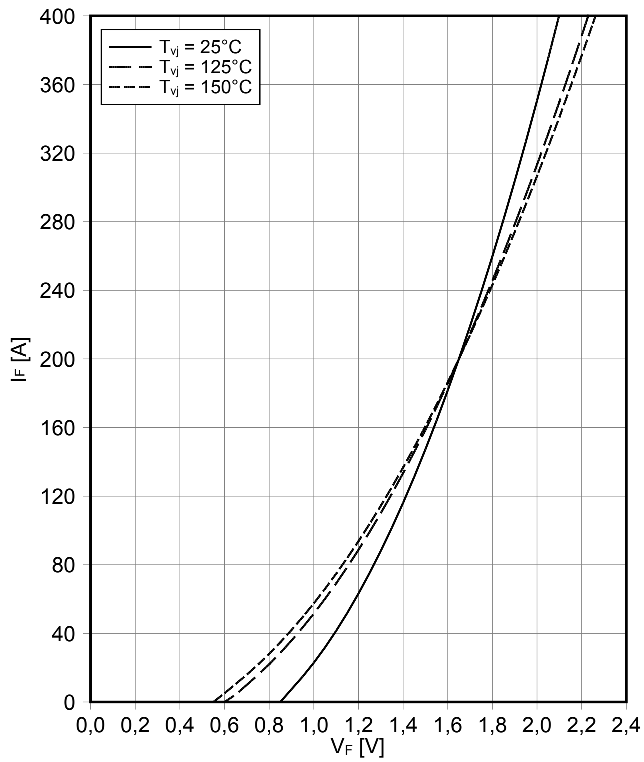
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT,Inverter
$Z_{thJH} = f(t)$



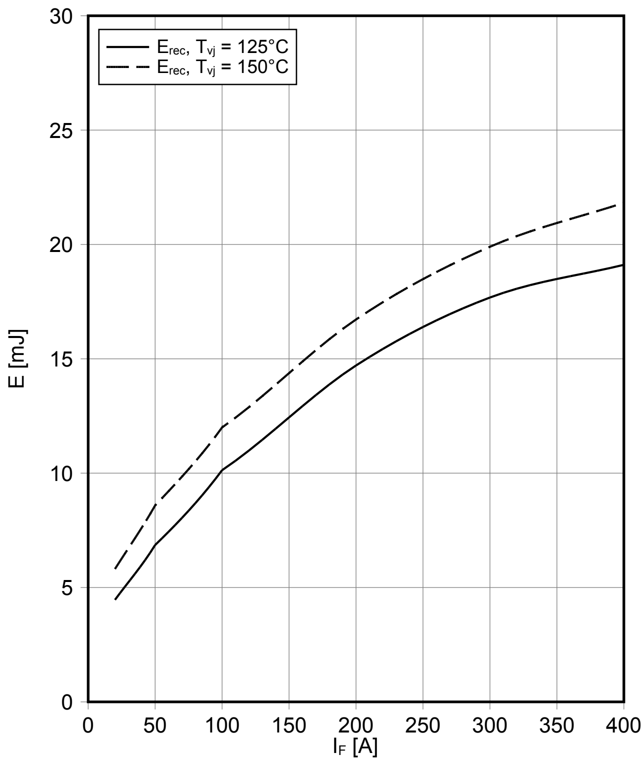
反偏安全工作区 IGBT, 逆变器 （RBSOA）
reverse bias safe operating area IGBT,Inverter (RBSOA)
$I_C = f(V_{CE})$
$V_{GE} = \pm15$ V, $R_{Goff} = 1.1\ \Omega$, $T_{vj} = 150$°C



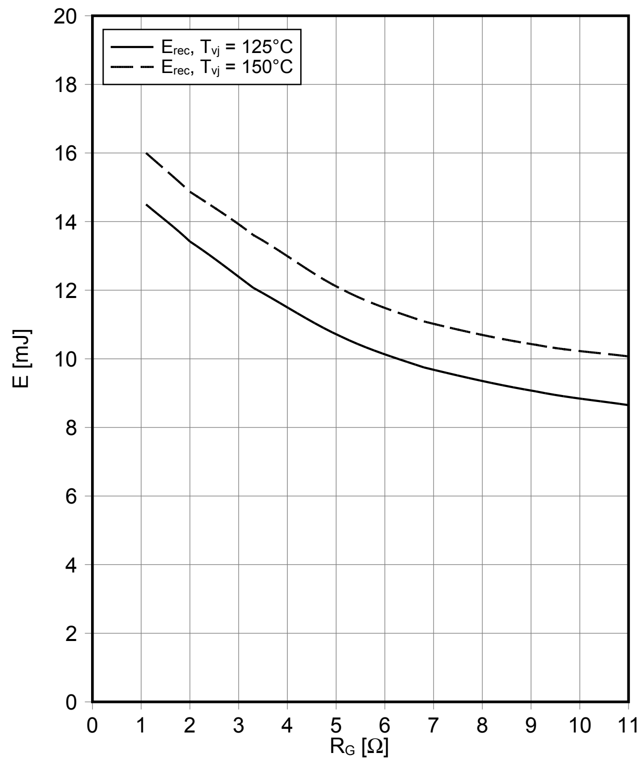
正向偏压特性 二极管,逆变器 （典型)
forward characteristic of Diode, Inverter (typical)
$I_F = f(V_F)$



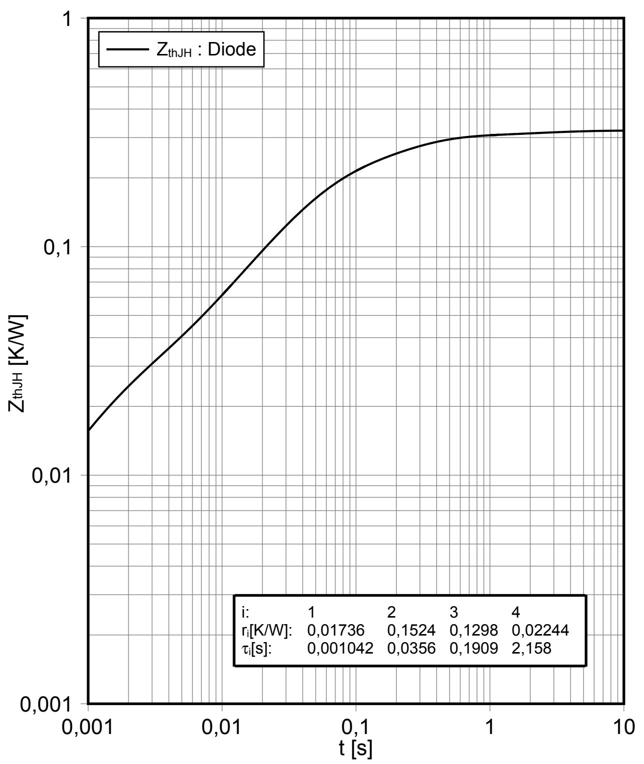
开关损耗 二极管,逆变器 （典型)
switching losses Diode, Inverter (typical)
$E_{rec} = f(I_F)$
R_{Gon} = 1.1 Ω, V_{CE} = 600 V



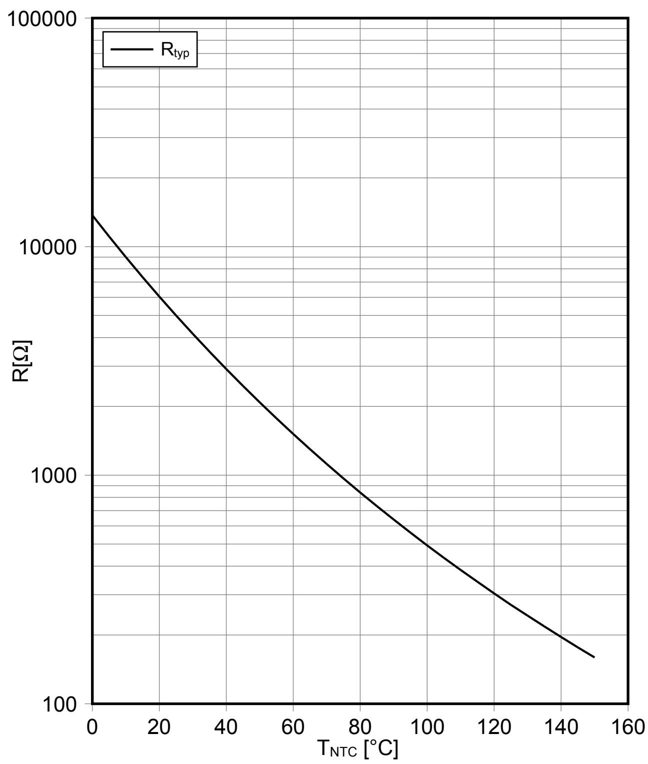
开关损耗 二极管,逆变器 （典型)
switching losses Diode, Inverter (typical)
$E_{rec} = f(R_G)$
I_F = 200 A, V_{CE} = 600 V



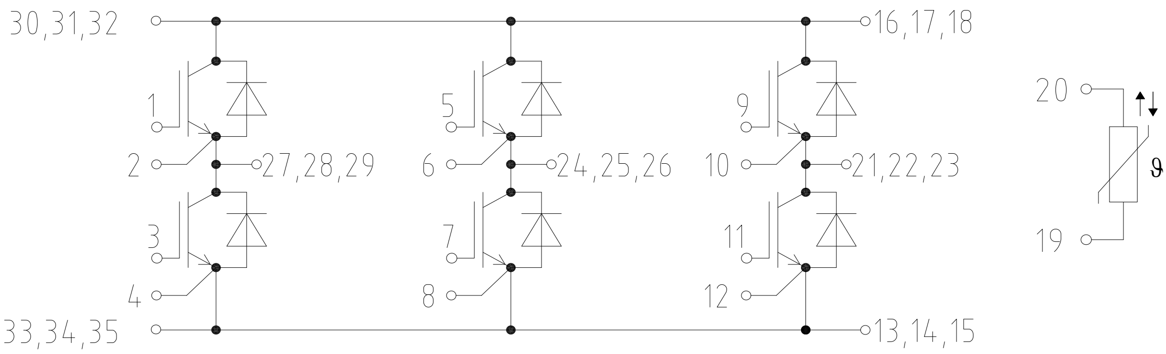
瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter
$Z_{thJH} = f(t)$



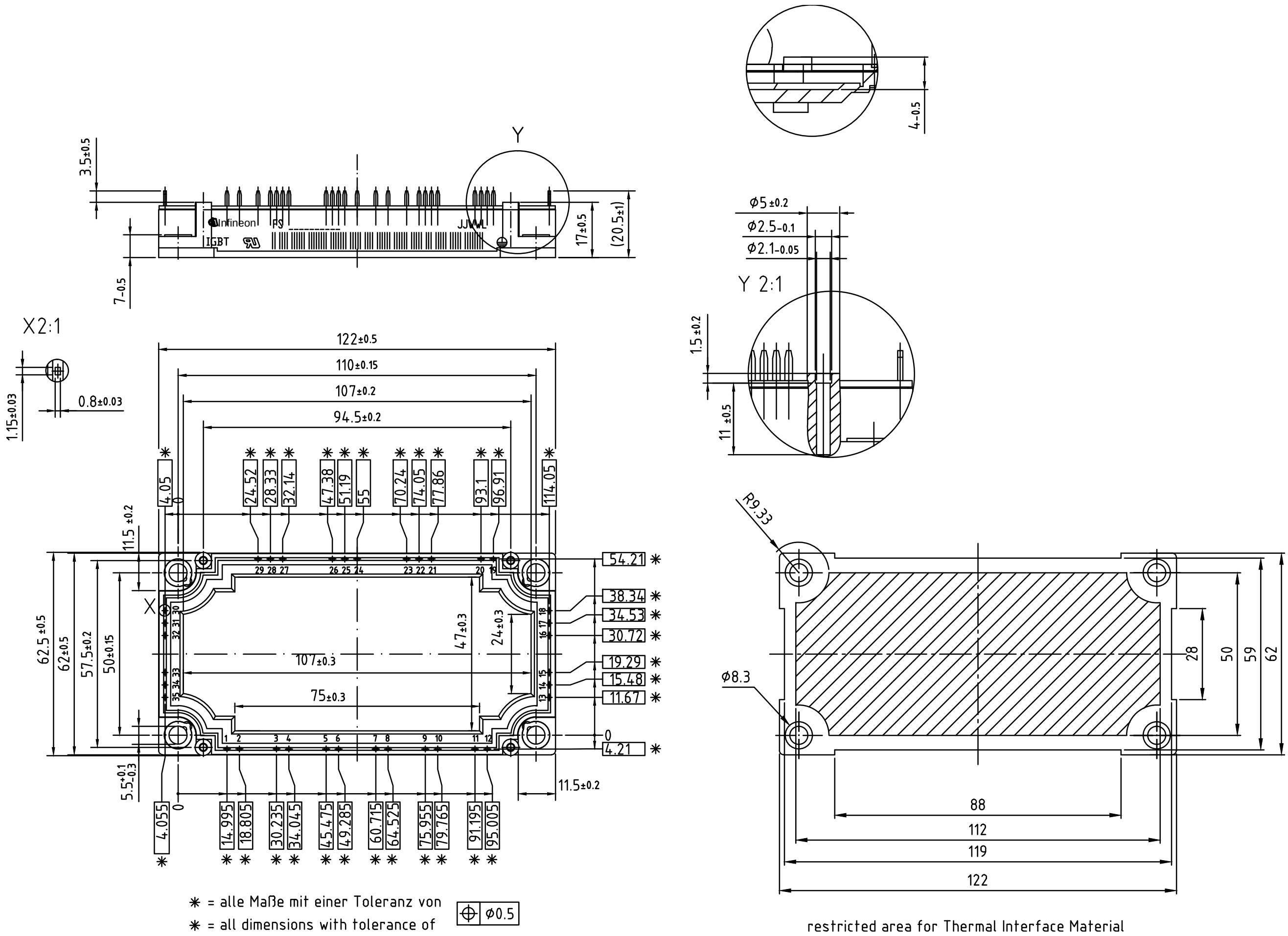
负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)
R = f (T)



接线图 / Circuit diagram



封装尺寸 / Package outlines



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